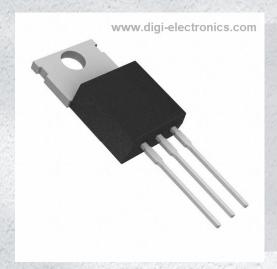


MJE5731AG Datasheet



https://www.DiGi-Electronics.com

DiGi Electronics Part Number MJE5731AG-DG

Manufacturer onsemi

Manufacturer Product Number MJE5731AG

Description TRANS PNP 375V 1A TO220

Detailed Description Bipolar (BJT) Transistor PNP 375 V 1 A 10MHz 40 W

Through Hole TO-220



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.



Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
MJE5731AG	onsemi
Series:	Product Status:
	Active
Transistor Type:	Current - Collector (Ic) (Max):
PNP	1 A
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:
375 V	1V @ 200mA, 1A
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
1mA	30 @ 300mA, 10V
Power - Max:	Frequency - Transition:
40 W	10MHz
Operating Temperature:	Mounting Type:
-65°C ~ 150°C (TJ)	Through Hole
Package / Case:	Supplier Device Package:
TO-220-3	TO-220
Base Product Number:	
MJE5731	

Environmental & Export classification

8541.29.0095

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	Not Applicable
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	



High Voltage PNP Silicon Plastic Power Transistors

MJE5730, MJE5731, MJE5731A

These devices are designed for line operated audio output amplifier, switch-mode power supply drivers and other switching applications.

Features

- Popular TO-220 Plastic Package
- PNP Complements to the TIP47 thru TIP50 Series
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage MJE5730 MJE5731 MJE5731A	V _{CEO}	300 350 375	Vdc
Collector-Base Voltage MJE5730 MJE5731 MJE5731A	V _{CB}	300 350 375	Vdc
Emitter-Base Voltage	V_{EB}	5.0	Vdc
Collector Current - Continuous	I _C	1.0	Adc
Collector Current - Peak	I _{CM}	3.0	Adc
Base Current	Ι _Β	1.0	Adc
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	40 0.32	W W/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	2.0 0.016	W W/°C
Unclamped Inducting Load Energy (See Figure 10)	Е	20	mJ
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

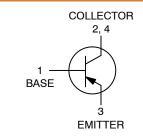
THERMAL CHARACTERISTICS

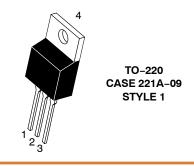
Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	3.125	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	°C/W

^{*}For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

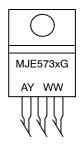
1

1.0 AMPERE POWER TRANSISTORS PCP SILICON 300-350-400 VOLTS 50 WATTS





MARKING DIAGRAM



MJE573x = Device Code

x = 0, 1, or 1A

G = Pb-Free Package A = Assembly Location

Y = Year WW = Work Week

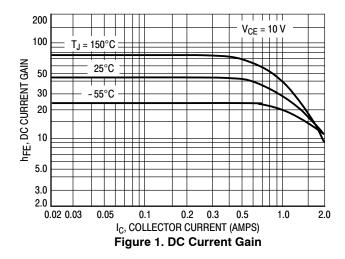
ORDERING INFORMATION

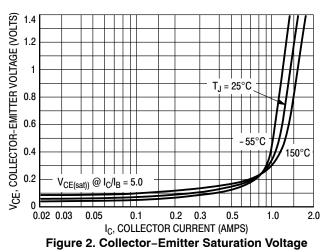
See detailed ordering and shipping information on page 5 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Sustaining Voltage (Note 1) $ \begin{pmatrix} I_C = 30 \text{ mAdc}, I_B = 0 \end{pmatrix} $ $ MJE5730 $ $ MJE5731 $ $ MJE5731A $	V _{CEO(sus)}	300 350 375	- - -	Vdc
Collector Cutoff Current $(V_{CE} = 200 \text{ Vdc}, I_B = 0)$ MJE5730 $(V_{CE} = 250 \text{ Vdc}, I_B = 0)$ MJE5731 $(V_{CE} = 300 \text{ Vdc}, I_B = 0)$ MJE5731A	I _{CEO}	- - -	1.0 1.0 1.0	mAdc
Collector Cutoff Current $ \begin{array}{l} (\text{V}_{\text{CE}} = 300 \text{ Vdc}, \text{V}_{\text{BE}} = 0) \\ \text{MJE5730} \\ (\text{V}_{\text{CE}} = 350 \text{ Vdc}, \text{V}_{\text{BE}} = 0) \\ \text{MJE5731} \\ (\text{V}_{\text{CE}} = 400 \text{ Vdc}, \text{V}_{\text{BE}} = 0) \\ \text{MJE5731A} \end{array} $	I _{CES}		1.0 1.0 1.0	mAdc
Emitter Cutoff Current (V _{BE} = 5.0 Vdc, I _C = 0)	I _{EBO}	-	1.0	mAdc
ON CHARACTERISTICS (Note 1)	•			
DC Current Gain $ \begin{pmatrix} I_C = 0.3 \text{ Adc, } V_{CE} = 10 \text{ Vdc} \\ I_C = 1.0 \text{ Adc, } V_{CE} = 10 \text{ Vdc} \end{pmatrix} $	h _{FE}	30 10	150 -	-
Collector-Emitter Saturation Voltage (I _C = 1.0 Adc, I _B = 0.2 Adc)	V _{CE(sat)}	-	1.0	Vdc
Base-Emitter On Voltage (I _C = 1.0 Adc, V _{CE} = 10 Vdc)	V _{BE(on)}	-	1.5	Vdc
DYNAMIC CHARACTERISTICS	•	•	•	
Current Gain – Bandwidth Product (I _C = 0.2 Adc, V _{CE} = 10 Vdc, f = 2.0 MHz)	f _T	10	-	MHz
Small–Signal Current Gain ($I_C = 0.2$ Adc, $V_{CE} = 10$ Vdc, $f = 1.0$ kHz)	h _{fe}	25	-	-
	•			

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.





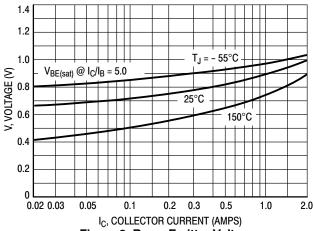


Figure 3. Base-Emitter Voltage

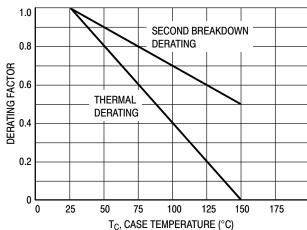


Figure 4. Normalized Power Derating

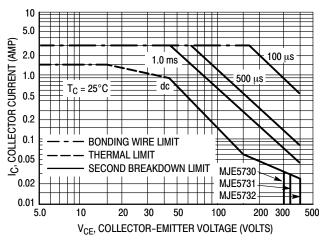


Figure 5. Forward Bias Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I_C – V_{CE} limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150^{\circ}\text{C}$; T_{C} is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 150^{\circ}\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 6. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

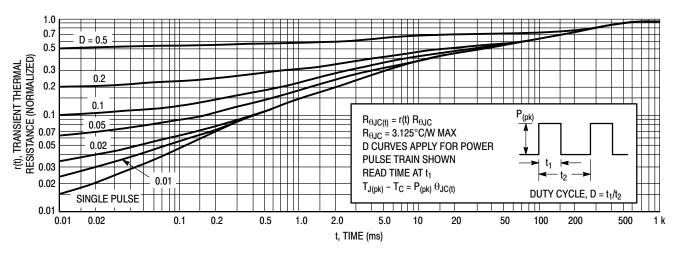


Figure 6. Thermal Response

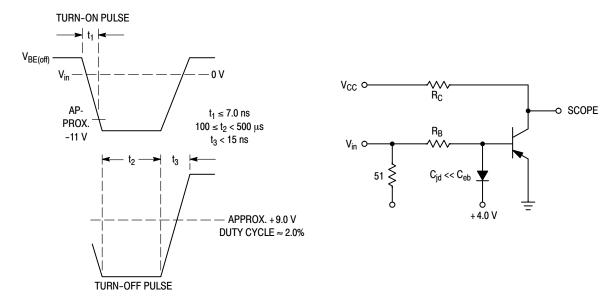


Figure 7. Switching Time Equivalent Circuit

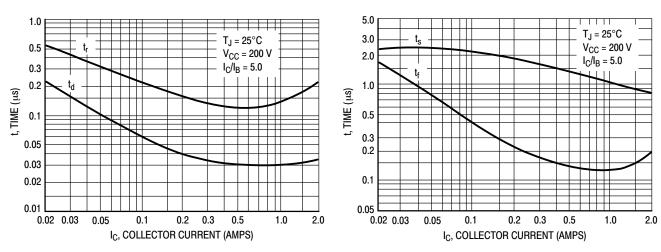
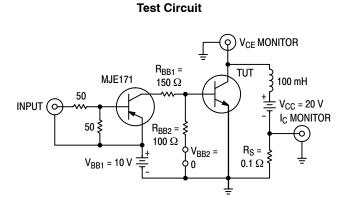


Figure 8. Turn-On Resistive Switching Times

Figure 9. Resistive Turn-Off Switching Times



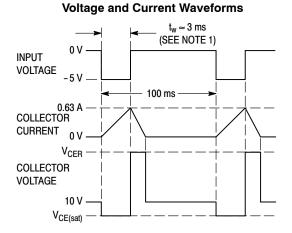


Figure 10. Inductive Load Switching

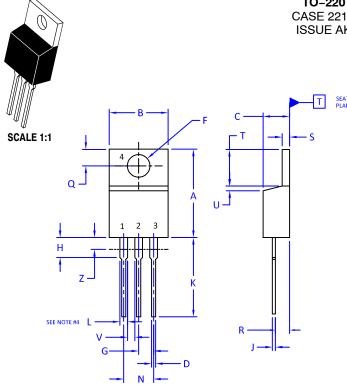
ORDERING INFORMATION

Device	Package	Shipping
MJE5730G	TO-220 (Pb-Free)	50 Units / Rail
MJE5731G	TO-220 (Pb-Free)	50 Units / Rail
MJE5731AG	TO-220 (Pb-Free)	50 Units / Rail

PACKAGE DIMENSIONS



DATE 13 JAN 2022



- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: INCHES
- 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.
- 4. MAX WIDTH FOR F102 DEVICE = 1.35MM

	INCH	IES	MILLIMETERS		
DIM	MIN.	MAX.	MIN.	MAX.	
Α	0.570	0.620	14.48	15.75	
В	0.380	0.415	9.66	10.53	
С	0.160	0.190	4.07	4.83	
D	0.025	0.038	0.64	0.96	
F	0.142	0.161	3.60	4.09	
G	0.095	0.105	2.42	2.66	
Н	0.110	0.161	2.80	4.10	
J	0.014	0.024	0.36	0.61	
К	0.500	0.562	12.70	14.27	
L	0.045	0.060	1.15	1.52	
N	0.190	0.210	4.83	5.33	
Q	0.100	0.120	2.54	3.04	
R	0.080	0.110	2.04	2.79	
S	0.045	0.055	1.15	1.41	
Т	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
V	0.045		1.15		
Z		0.080		2.04	

STYLE 1: PIN 1. 2. 3. 4.	BASE COLLECTOR EMITTER COLLECTOR	2. 3.	BASE EMITTER COLLECTOR EMITTER	3.	CATHODE ANODE GATE ANODE	STYLE 4: PIN 1. 2. 3. 4.	MAIN TERMINAL 1 MAIN TERMINAL 2 GATE MAIN TERMINAL 2
STYLE 5:		STYLE 6:		STYLE 7:		STYLE 8:	
PIN 1.	GATE	PIN 1.	ANODE	PIN 1.	CATHODE	PIN 1.	CATHODE
2.	DRAIN	2.	CATHODE	2.	ANODE	2.	ANODE
3.	SOURCE	3.	ANODE	3.	CATHODE	3.	EXTERNAL TRIP/DELAY
4.	DRAIN	4.	CATHODE	4.	ANODE	4.	ANODE
STYLE 9:		STYLE 10:		STYLE 11:		STYLE 12:	:
PIN 1.	GATE	PIN 1.	GATE	PIN 1.	DRAIN	PIN 1.	MAIN TERMINAL 1
2.	COLLECTOR	2.	SOURCE	2.	SOURCE	2.	MAIN TERMINAL 2
3.	EMITTER	3.	DRAIN	3.	GATE	3.	GATE
4.	COLLECTOR	4.	SOURCE	4.	SOURCE	4.	NOT CONNECTED

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